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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HAF2014

Silicon N Channel MOS FET Series Power Switching

RENESAS

ADE-208-953 (Z)
1st.Edition
July 2000

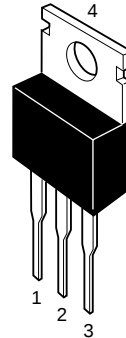
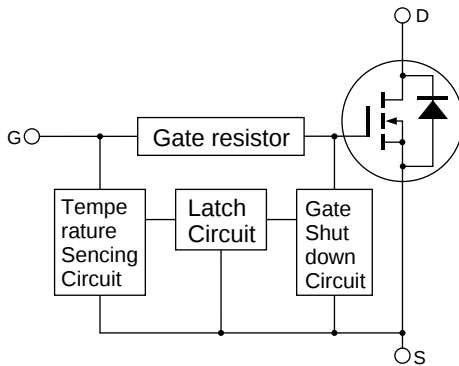
This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

- Logic level operation (4 to 6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut-down operation (Need 0 voltage recovery)

Outline

TO-220AB



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	60	V
Gate to source voltage	V_{GS}	16	V
Gate to source voltage	V_{GS}	-2.5	V
Drain current	I_D	40	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	80	A
Body-drain diode reverse drain current	I_{DR}	40	A
Channel dissipation	P_{ch} ^{Note2}	50	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

2. Value at Ta = 25°C

Typical Operation Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	3.5	—	—	V	
	V_{IL}	—	—	1.2	V	
Input current (Gate non shut down)	I_{IH1}	—	—	100	μA	$V_i = 8V, V_{DS} = 0$
	I_{IH2}	—	—	50	μA	$V_i = 3.5V, V_{DS} = 0$
	I_{IL}	—	—	1	μA	$V_i = 1.2V, V_{DS} = 0$
Input current (Gate shut down)	$I_{IH(sd)1}$	—	0.8	—	mA	$V_i = 8V, V_{DS} = 0$
	$I_{IH(sd)2}$	—	0.35	—	mA	$V_i = 3.5V, V_{DS} = 0$
Shut down temperature	T_{sd}	—	175	—	°C	Channel temperature
Gate operation voltage	V_{OP}	3.5	—	12	V	

Electrical Characteristics (Ta = 25°C)

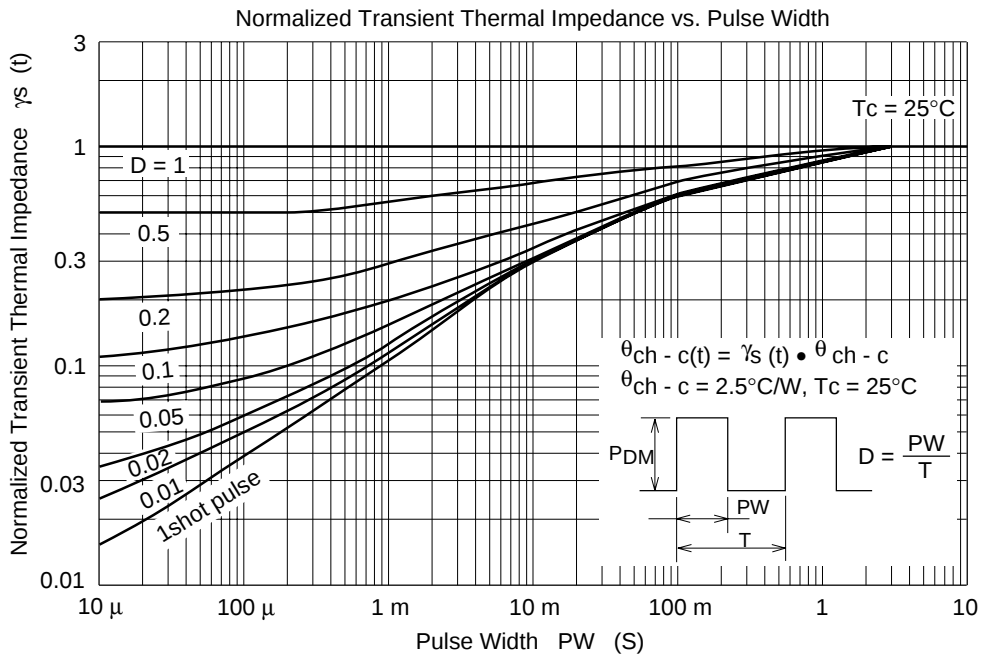
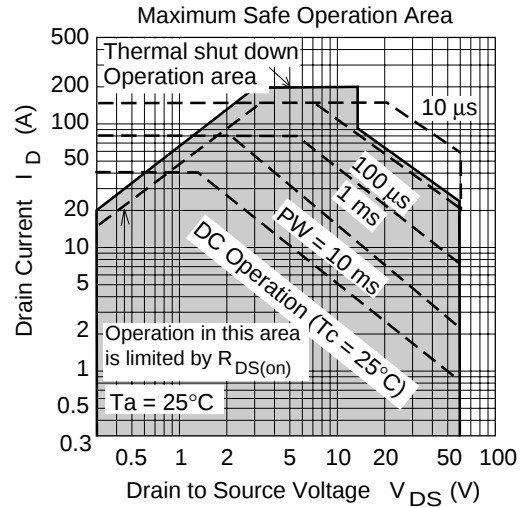
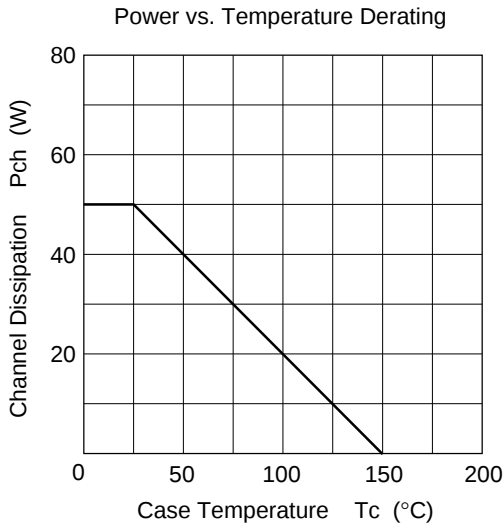
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	15	—	—	A	$V_{GS} = 3.5V, V_{DS} = 2V$
Drain current	I_{D2}	—	—	10	mA	$V_{GS} = 1.2V, V_{DS} = 2V$
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	16	—	—	V	$I_G = 300\mu A, V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-2.5	—	—	V	$I_G = -100\mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS1}	—	—	100	μA	$V_{GS} = 8V, V_{DS} = 0$
	I_{GSS2}	—	—	50	μA	$V_{GS} = 3.5V, V_{DS} = 0$
	I_{GSS3}	—	—	1	μA	$V_{GS} = 1.2V, V_{DS} = 0$
	I_{GSS4}	—	—	-100	μA	$V_{GS} = -2.4V, V_{DS} = 0$
Input current (shut down)	$I_{GS(op)1}$	—	0.8	—	mA	$V_{GS} = 8V, V_{DS} = 0$
	$I_{GS(op)2}$	—	0.35	—	mA	$V_{GS} = 3.5V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.25	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	25	33	m Ω	$I_D = 20A, V_{GS} = 4V$ ^{Note3}
Static drain to source on state resistance	$R_{DS(on)}$	—	15	20	m Ω	$I_D = 20A, V_{GS} = 10V$ ^{Note3}
Forward transfer admittance	$ y_{fs} $	8	16	—	S	$I_D = 20A, V_{DS} = 10V$ ^{Note3}
Output capacitance	Coss	—	940	—	pF	$V_{DS} = 10V, V_{GS} = 0$ $f = 1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	10.7	—	μs	$I_D = 20A, V_{GS} = 5V$ $R_L = 1.5\Omega$
Rise time	t_r	—	66	—	μs	
Turn-off delay time	$t_{d(off)}$	—	15.5	—	μs	
Fall time	t_f	—	19	—	μs	
Body-drain diode forward voltage	V_{DF}	—	1	—	V	$I_F = 40A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = 40A, V_{GS} = 0$ $di_F/dt = 50A/\mu s$
Over load shut down operation time ^{Note4}	t_{os1}	—	1	—	ms	$V_{GS} = 5V, V_{DD} = 16V$

Note: 3. Pulse test

4. Including the junction temperature rise of the over loaded condition.

See characteristic curve of HAF2005.

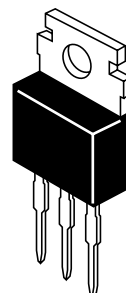
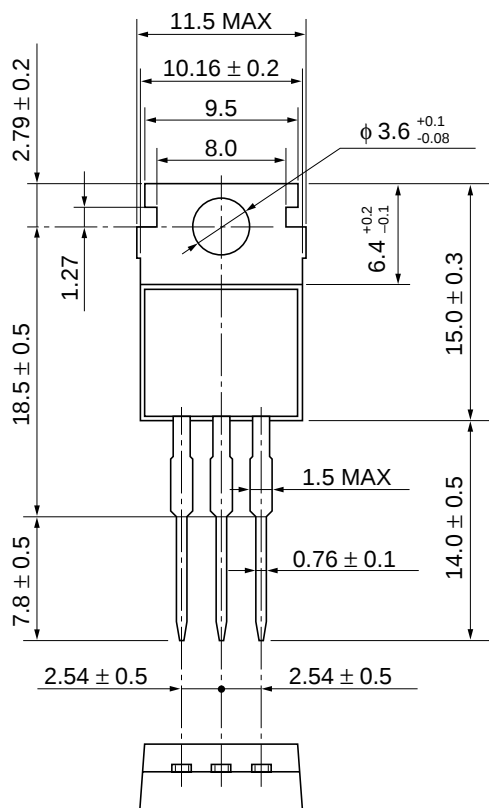
Main Characteristics



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	:	http://semiconductor.hitachi.com/
	Europe	:	http://www.hitachi-eu.com/hel/ecg
	Asia	:	http://sicapac.hitachi-asia.com
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For further information write to:Hitachi Semiconductor
(America) Inc.179 East Tasman Drive,
San Jose, CA 95134

Tel: <1> (408) 433-1990

Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components GroupDornacher Straße 3
D-85622 Feldkirchen, Munich

Germany

Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.

Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000

Fax: <44> (1628) 585160

Hitachi Asia Ltd.

Hitachi Tower

16 Collyer Quay #20-00,

Singapore 049318

Tel: <65>-538-6533/538-8577

Fax: <65>-538-6933/538-3877

URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.

(Taipei Branch Office)

4/F, No. 167, Tun Hwa North Road,

Hung-Kuo Building,

Taipei (105), Taiwan

Tel: <886>-(2)-2718-3666

Fax: <886>-(2)-2718-8180

Telex: 23222 HAS-TP

URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.

Group III (Electronic Components)

7/F., North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon,

Hong Kong

Tel: <852>-(2)-735-9218

Fax: <852>-(2)-730-0281

URL: <http://www.hitachi.com.hk>